

AMENDMENTS TO THE ABSTRACT

Please replace the abstract with the following amended abstract:

A method of fabricating a thin film transistor includes providing a substrate; depositing amorphous silicon on the substrate; patterning the amorphous silicon to form a plurality of island-shaped amorphous silicon layers; forming spaces between the substrate and the amorphous silicon layers; forming a channel region, a source ohmic contact region, and a drain ohmic contact region on each of the amorphous silicon layers by ion doping the island-shaped amorphous silicon layers; forming a first insulating layer over the amorphous silicon layers; crystallizing the plurality of the island-shaped amorphous silicon layers to form a plurality of an island-shaped polysilicon layers by irradiating laser beams onto the first insulating layer, wherein the plurality of the island-shaped polysilicon layers are the active layers of the thin film transistor; forming a gate electrode on the first insulating layer; and forming source and drain electrodes that contact the source and drain ohmic contact regions, respectively. The spaces formed between the substrate and silicon layers increase the grain size of the polysilicon layers. ~~a substrate having an upper side; a plurality of parallel-connected active layers supported on the upper side of the substrate; spaces defined between the substrate and the active layers; a first insulating layer on the plurality of active layers; a gate electrode on the first insulating layer over the plurality of active layers; and source and drain electrodes contacting the plurality of the active layers. The active layers of the thin film transistor are laser annealed to polycrystalline silicon. The spaces result in large polysilicon grains that result in good electrical characteristics.~~